1. General description

NPN high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

PNP complement: PHPT60610PY

2. Features and benefits

- · High thermal power dissipation capability
- · High temperature applications up to 175 °C
- · Reduced Printed Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified.

3. Applications

- · Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	60	V
I _C	collector current		-	-	10	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	20	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 10 A; I_B = 1 A; $t_p \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	25	36	mΩ



60 V, 10 A NPN high power bipolar transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	С
2	Е	emitter		
3	Е	emitter	a	B —
4	В	base	0 0 0 0	Ė
mb	С	collector	1 2 3 4	sym123
			LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number Package					
	Name	Description	Version		
PHPT60610NY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT60610NY	0610NAB

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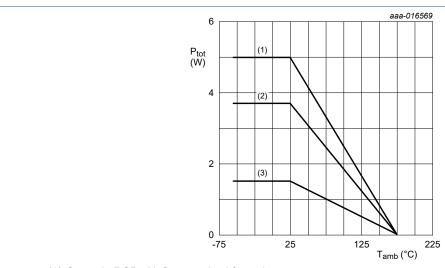
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	60	V
V _{CEO}	collector-emitter voltage	open base		-	60	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	10	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	20	Α
I _B	base current			-	1.5	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB); single-sided copper; tin-plated and standard footprint.
- Device mounted on an FR4 PCB; single-sided copper; tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB; Al₂O₃, standard footprint.
- [4] Power dissipation from junction to mounting base.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

60 V, 10 A NPN high power bipolar transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Cumphal	Downwoodow	Canditions		BA:	T	Mass	11
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air	[1]	-	-	100	K/W
	junction to ambient	[2]	[2]	-	-	41	K/W
			[3]	-	-	30	K/W
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

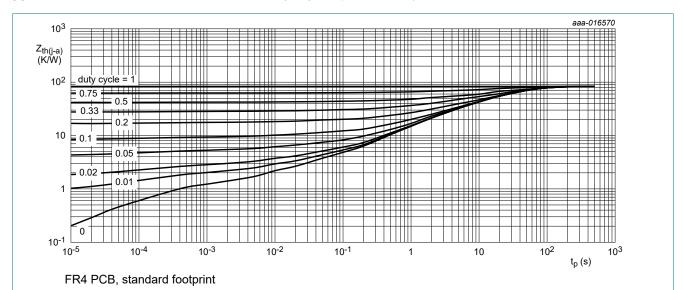


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

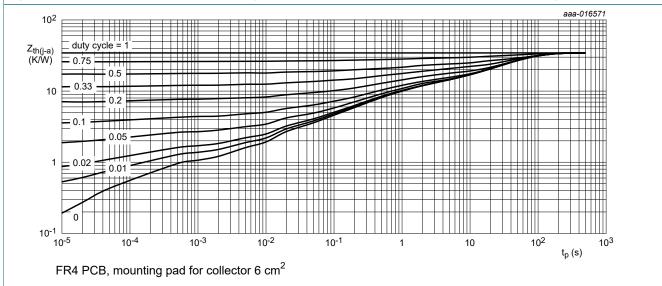


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

60 V, 10 A NPN high power bipolar transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 48 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = 48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA; T _{amb} = 25 °C	240	410	-	
		V_{CE} = 2 V; I_{C} = 1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	210	400	-	
		V_{CE} = 2 V; I_{C} = 5 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	200	-	
		V_{CE} = 2 V; I_{C} = 10 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	50	100	-	
V _{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C; pulsed	-	30	40	mV
		I_C = 5 A; I_B = 500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	115	160	mV
		I_C = 10 A; I_B = 1 A; $t_p \le 300 \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	250	360	mV
R _{CEsat}	collector-emitter saturation resistance		-	25	36	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; $t_p \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	0.95	V
		I_C = 5 A; I_B = 500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.2	V
		I_C = 10 A; I_B = 1 A; $t_p \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.4	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2 \text{ V}; I_{C} = 500 \text{ mA}; T_{amb} = 25 \text{ °C}$	-	-	0.8	V
t _d	delay time	V _{CC} = 12.5 V; I _C = 5 A; I _{Bon} = 250 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -250 mA; T _{amb} = 25 °C	-	180	-	ns
t _{on}	turn-on time		-	200	-	ns
t _s	storage time		-	340	-	ns
t _f	fall time		-	165	-	ns
t _{off}	turn-off time		-	505	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 500 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	50	-	pF

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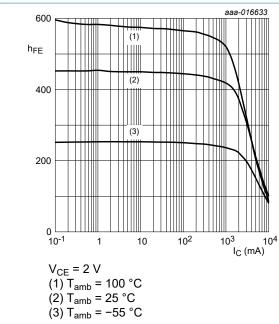
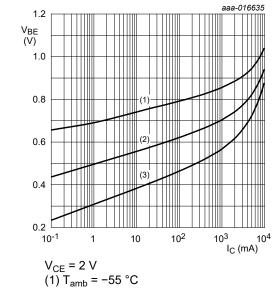


Fig. 4. DC current gain as a function of collector current; typical values



(2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Base-emitter voltage as a function of collector Fig. 6. current; typical values

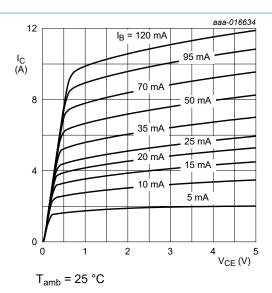
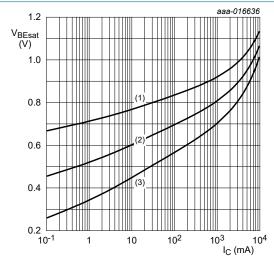


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



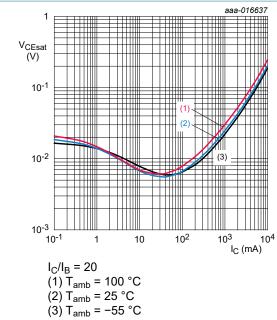
 $I_{\rm C}/I_{\rm B}=20$ (1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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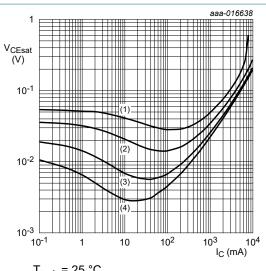


$$(1) T_{amb} = 100 °($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1) $I_{C}/I_{B} = 100$

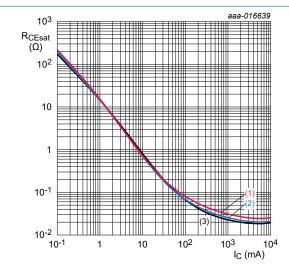
$$(1) I_{\rm C}/I_{\rm B} = 10$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_{\rm C}/I_{\rm B} = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



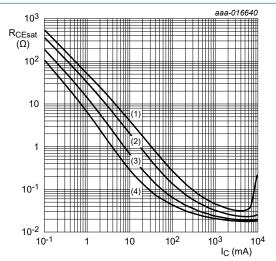
$$I_{\rm C}/I_{\rm B}=20$$

$$(1) T_{amb} = 100 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \,^{\circ}C$$

(1) $I_C/I_B = 100$

$$(2) I_{\rm C}/I_{\rm B} = 50$$

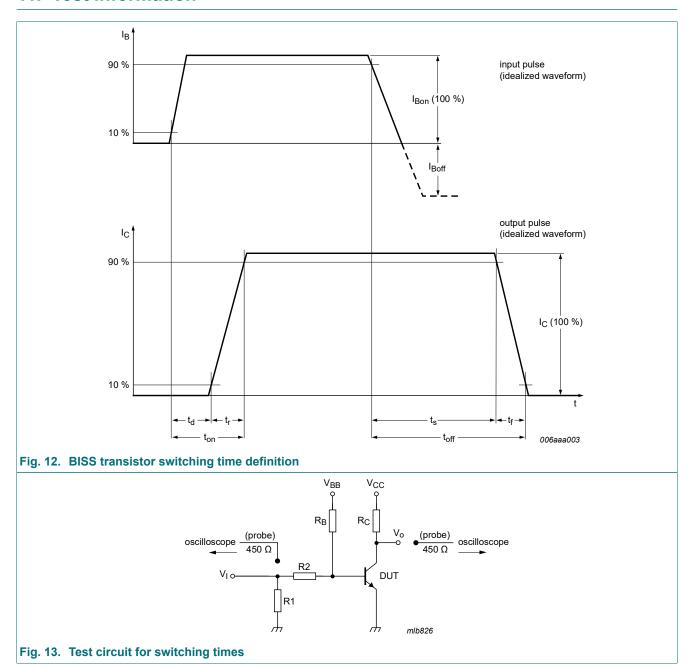
(3)
$$I_C/I_B = 20$$

 $(4) I_C/I_B = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline

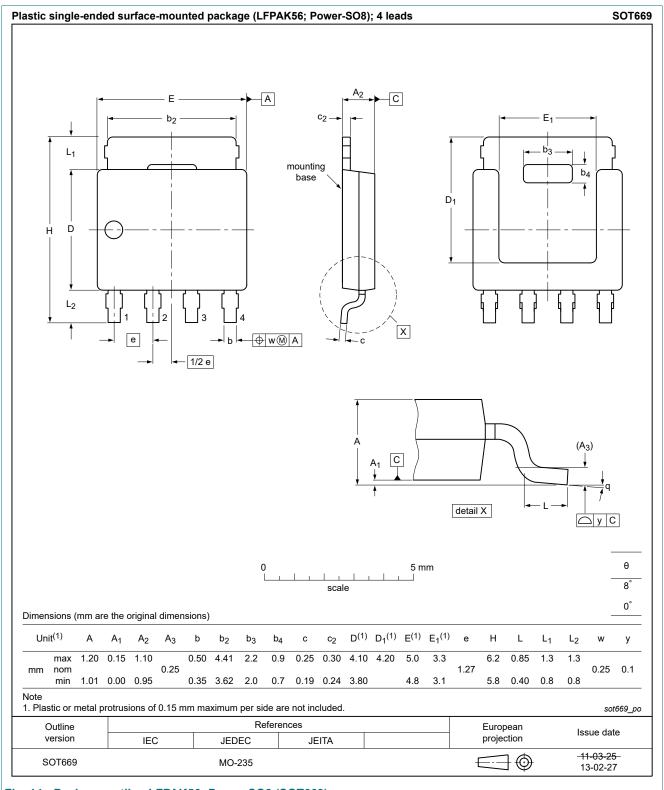
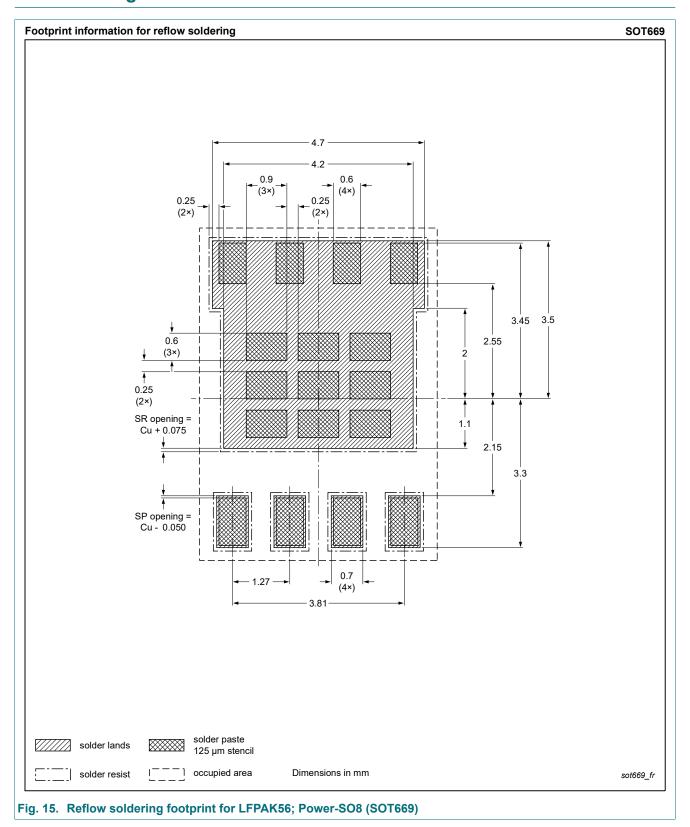


Fig. 14. Package outline LFPAK56; Power-SO8 (SOT669)

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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PHPT60610NY v.2	20190115	Product data sheet	-	PHPT60610NY v.1				
Modifications:	Typo at figures 2 and 3: unit corrected from ns to s at x-scale							
PHPT60610NY v.1	20150527	Product data sheet	-	-				

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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